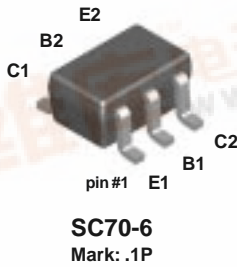


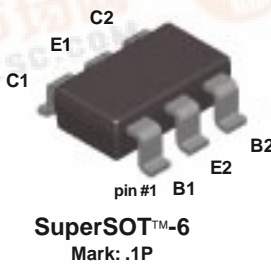


Discrete POWER & Signal Technologies

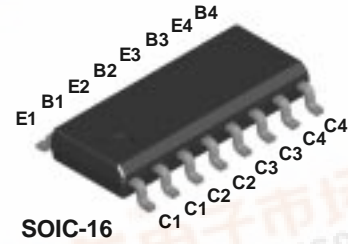
**FFB2222A**



**FMB2222A**



**MMPQ2222A**



**NPN Multi-Chip General Purpose Amplifier**

This device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from Process 19.

**Absolute Maximum Ratings\*** T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	75	V
V <sub>EBO</sub>	Emitter-Base Voltage	6.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

**Thermal Characteristics** T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Characteristic	Max			Units
		FFB2222A	FMB2222A	MMPQ2222A	
P <sub>D</sub>	Total Device Dissipation	300	700	1,000	mW
	Derate above 25°C	2.4	5.6	8.0	mW/°C
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	415	180		°C/W
	Effective 4 Die			125	°C/W
	Each Die			240	°C/W



## NPN Multi-Chip General Purpose Amplifier

(continued)

### Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

#### OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10\text{ mA}, I_B = 0$	40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\text{ }\mu\text{A}, I_E = 0$	75			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	6.0			V
$I_{CEX}$	Collector Cutoff Current	$V_{CE} = 60\text{ V}, V_{EB(OFF)} = 3.0\text{ V}$			10	nA
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = 60\text{ V}, I_E = 0$ $V_{CB} = 60\text{ V}, I_E = 0, T_A = 125^\circ\text{C}$			0.01 10	$\mu\text{A}$ $\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = 3.0\text{ V}, I_C = 0$			10	nA
$I_{BL}$	Base Cutoff Current	$V_{CE} = 60\text{ V}, V_{EB(OFF)} = 3.0\text{ V}$			20	nA

#### ON CHARACTERISTICS

$h_{FE}$	DC Current Gain	$I_C = 0.1\text{ mA}, V_{CE} = 10\text{ V}$	35			
		$I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}$	50			
		$I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$	75			
		$I_C = 10\text{ mA}, V_{CE} = 10\text{ V}, T_A = -55^\circ\text{C}$	35			
		$I_C = 150\text{ mA}, V_{CE} = 10\text{ V}^*$	100		300	
		$I_C = 150\text{ mA}, V_{CE} = 1.0\text{ V}^*$	50			
	$I_C = 500\text{ mA}, V_{CE} = 10\text{ V}^*$	40				
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage*	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$			0.3 1.0	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage*	$I_C = 150\text{ mA}, I_B = 1.0\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$	0.6		1.2 2.0	V V

#### SMALL SIGNAL CHARACTERISTICS

$f_T$	Current Gain - Bandwidth Product	$I_C = 20\text{ mA}, V_{CE} = 20\text{ V},$ $f = 100\text{ MHz}$		300		MHz
$C_{obo}$	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 100\text{ kHz}$		4.0		pF
$C_{ibo}$	Input Capacitance	$V_{EB} = 0.5\text{ V}, I_C = 0, f = 100\text{ kHz}$		20		pF
NF	Noise Figure	$I_C = 100\text{ }\mu\text{A}, V_{CE} = 10\text{ V},$ $R_S = 1.0\text{ k}\Omega, f = 1.0\text{ kHz}$		2.0		dB

#### SWITCHING CHARACTERISTICS

$t_d$	Delay Time	$V_{CC} = 30\text{ V}, V_{BE(OFF)} = 0.5\text{ V},$		8		ns
$t_r$	Rise Time	$I_C = 150\text{ mA}, I_{B1} = 15\text{ mA}$		20		ns
$t_s$	Storage Time	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA},$		180		ns
$t_f$	Fall Time	$I_{B1} = I_{B2} = 15\text{ mA}$		40		ns

\*Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

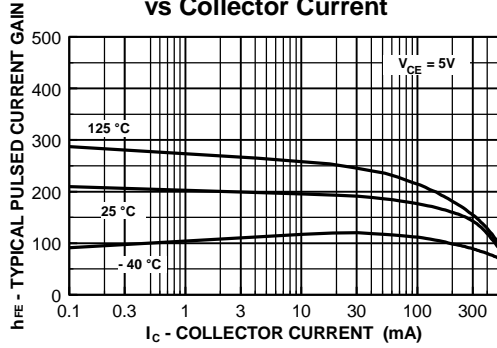
FFB2222A / FMB2222A / MMPQ2222A

# NPN Multi-Chip General Purpose Amplifier

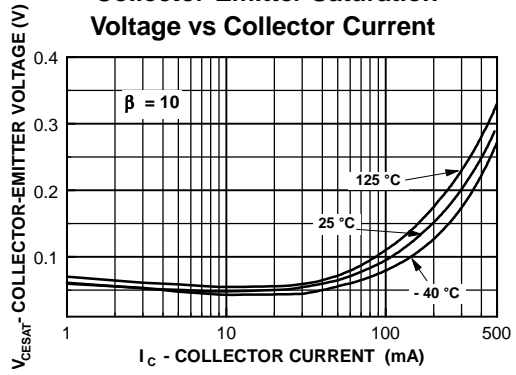
(continued)

## Typical Characteristics

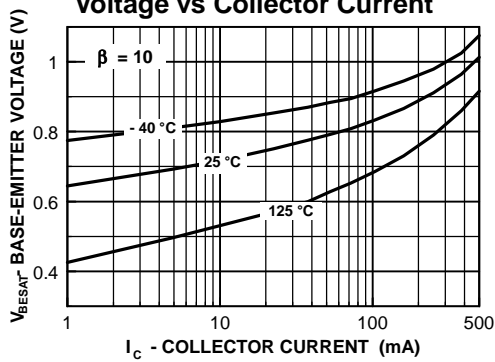
**Typical Pulsed Current Gain vs Collector Current**



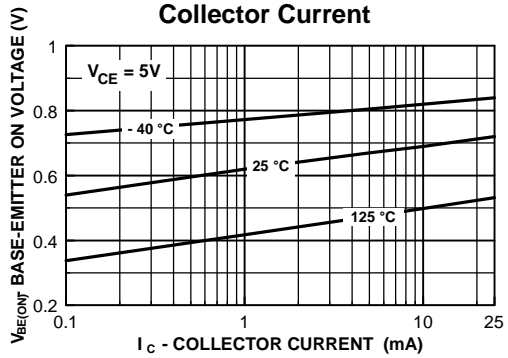
**Collector-Emitter Saturation Voltage vs Collector Current**



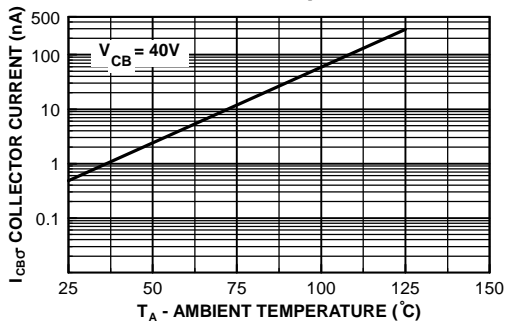
**Base-Emitter Saturation Voltage vs Collector Current**



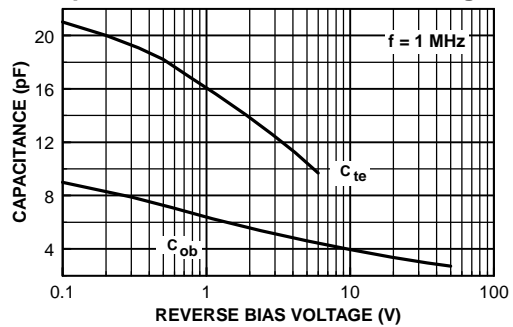
**Base-Emitter ON Voltage vs Collector Current**



**Collector-Cutoff Current vs Ambient Temperature**



**Emitter Transition and Output Capacitance vs Reverse Bias Voltage**



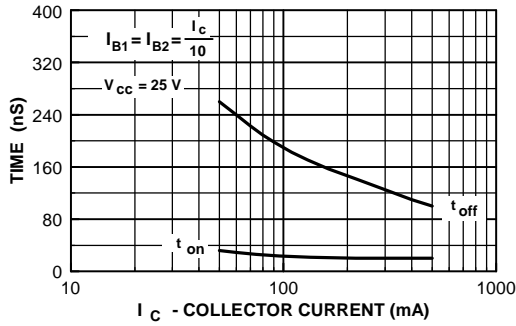
FFB2222A / FMB2222A / MMPQ2222A

# NPN Multi-Chip General Purpose Amplifier

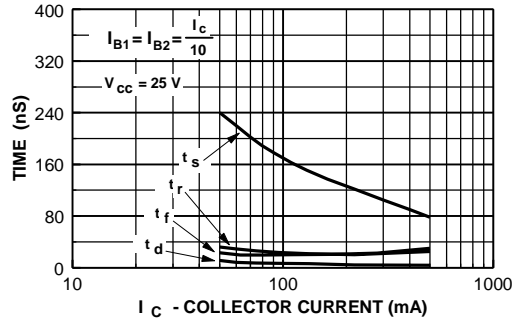
(continued)

## Typical Characteristics (continued)

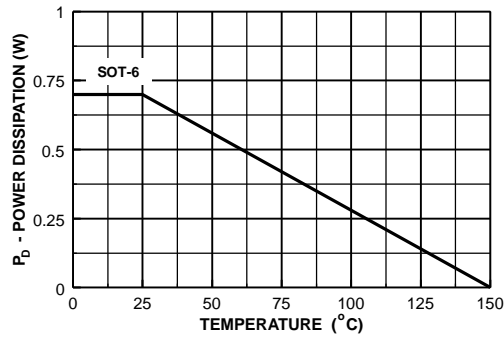
**Turn On and Turn Off Times vs Collector Current**



**Switching Times vs Collector Current**



**Power Dissipation vs Ambient Temperature**



FFB2222A / FMB2222A / MMPQ2222A

# NPN Multi-Chip General Purpose Amplifier

(continued)

## Test Circuits

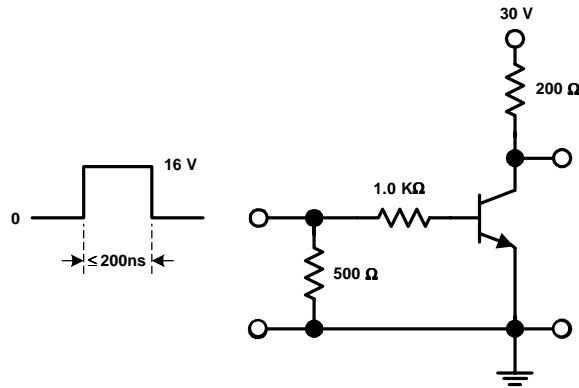


FIGURE 1: Saturated Turn-On Switching Time

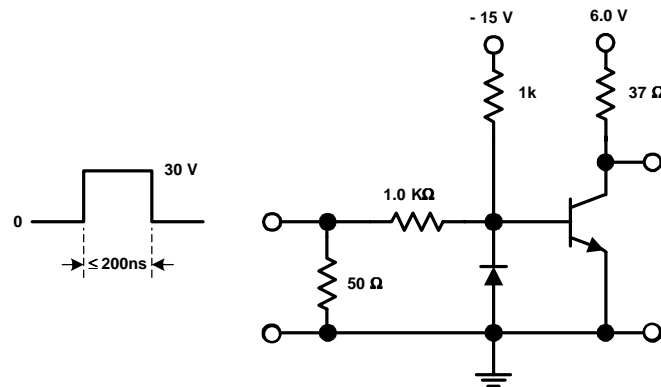


FIGURE 2: Saturated Turn-Off Switching Time